

**DESCRIPTION**

The SD1012-03 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications in the 36 – 175 MHz frequency range. Emitter ballasting is employed to achieve excellent ruggedness under severe load mismatch conditions.

**IMPORTANT:** For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

**KEY FEATURES**

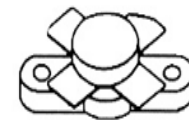
- 175 MHz
- 12.5 Volts
- Efficiency 50%
- Common Emitter
- $P_{OUT} = 6$  W Min.
- $G_P = 9$  dB Gain

**APPLICATIONS/BENEFITS**

- VHF Mobile Applications

**ABSOLUTE MAXIMUM RATINGS (T<sub>CASE</sub> = 25°C)**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	36	V
$V_{CEO}$	Collector-Emitter Voltage	18	V
$V_{CES}$	Collector-Emitter Voltage	36	V
$V_{EBO}$	Emitter-Base Voltage	4.0	V
$I_C$	Device Current	1.8	A
$P_{DISS}$	Power Dissipation (+25°C)	20	W
$T_J$	Junction Temperature	+200	°C
$T_{STG}$	Storage Temperature	-65 to +150	°C

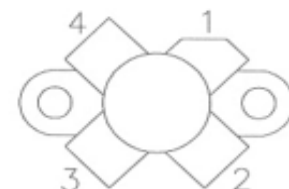


.380 4LFL (M113)  
epoxy sealed

**THERMAL DATA**

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	8.75	°C/W
---------------	----------------------------------	------	------

**PIN CONNECTION**



1. Collector      3. Base  
2. Emitter        4. Emitter

**STATIC ELECTRICAL SPECIFICATIONS (T<sub>CASE</sub> = 25°C)**

Symbol	Test Conditions	SD1012-03			Units
		Min.	Typ.	Max.	
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 5 mA</b>	36	—	—	V
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 10 mA</b>	18	—	—	V
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 1 mA</b>	4.0	—	—	V
<b>I<sub>CES</sub></b>	<b>V<sub>CB</sub> = 15 V</b>	—	—	1.0	mA
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V      I<sub>C</sub> = 250 mA</b>	5	—	—	—

**DYNAMIC ELECTRICAL SPECIFICATIONS (T<sub>CASE</sub> = 25°C)**

Symbol	Test Conditions	SD1012-03			Units
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 175 MHz    P<sub>IN</sub> = 0.75 W    V<sub>CC</sub> = 12.5 V</b>	6.0	—	—	W
<b>η<sub>C</sub></b>	<b>f = 175 MHz    P<sub>IN</sub> = 0.75 W    V<sub>CC</sub> = 12.5 V</b>	50	—	—	%
<b>G<sub>P</sub></b>	<b>f = 175 MHz    P<sub>IN</sub> = 0.75 W    V<sub>CC</sub> = 12.5 V</b>	9.0	—	—	dB
<b>C<sub>OB</sub></b>	<b>f = 1 MHz      V<sub>CB</sub> = 15 V</b>	—	—	20	pF

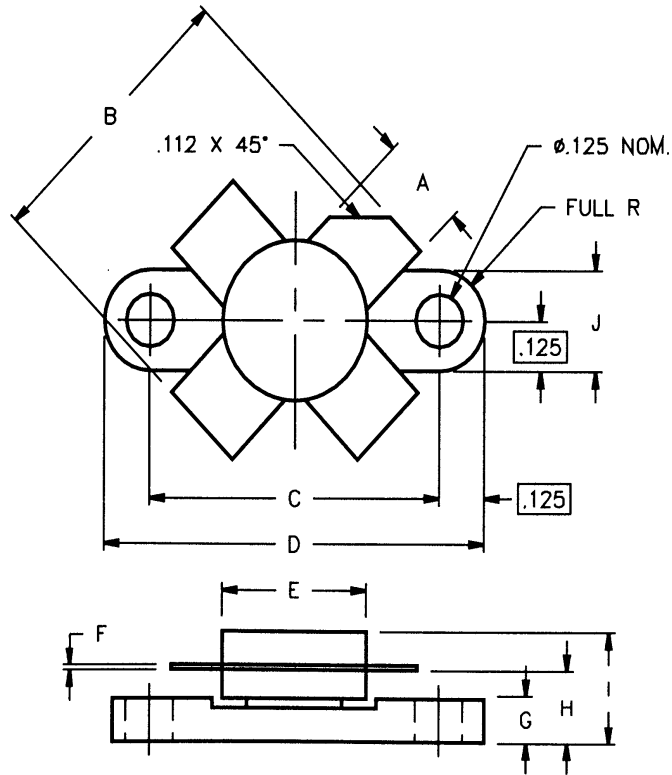
**IMPEDANCE DATA**

Freq.	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
150 MHz	4.90 + j 3.46	11.4 + j 4.56
175 MHz	4.32 + j 3.04	13.0 + j 7.81

**V<sub>CC</sub> = 12.5 V**

**P<sub>IN</sub> = 1 W**

PACKAGE STYLE M 113



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84	I		.260/7,11
B	.785/19,94		J	.240/6,10	.255/6,48
C	.720/18,29	.730/18,54			
D	.970/24,64	.980/24,89			
E		.385/9,78			
F	.004/0,10	.006/0,15			
G	.085/2,16	.105/2,67			
H	.160/4,06	.180/4,57			



SD1012-03

RF & MICROWAVE TRANSISTORS

PRODUCT PREVIEW

www.Microsemi.com

NOTES